**Product data sheet** 

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

### 2. Features and benefits

- · 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- · High immunity to false turn-on by dV/dt
- High voltage capability
- · Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only

## 3. Applications

- · Electronic thermostats
- General purpose motor controls
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions   | Mi | n Typ | Max | Unit |
|---------------------|--|--|----|-------|-----|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |  | -  | -     | 800 | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ ; $\overline{\text{Fig. 1}}$ ; $\overline{\text{Fig. 2}}$ ; $\overline{\text{Fig. 3}}$ | -  | -     | 8   | А    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)}$ = 25 °C;<br>$t_p$ = 20 ms; Fig. 4; Fig. 5  | -  | -     | 65  | А    |
|                     |  | full sine wave; $T_{j(init)}$ = 25 °C;<br>$t_p$ = 16.7 ms  | -  | -     | 71  | А    |
| Tj                  | junction temperature                     |  | -  | -     | 125 | °C   |
| Static chara        | acteristics                              |  |    |       | ,   | ,    |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } Fig. 7$   | 2  | 18    | 50  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$<br>$T_j = 25 \text{ °C; } Fig. 7$  | 2  | 21    | 50  | mA   |

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| Symbol                | Parameter                             | Conditions  | Min  | Тур  | Max  | Unit |
|-----------------------|---------------------------------------|---|------|------|------|------|
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$                          | 2    | 34   | 50   | mA   |
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>  | -    | 31   | 60   | mA   |
| V <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>   | -    | 1.3  | 1.65 | V    |
| Dynamic char          | acteristics                           |   |      |      |      |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 535 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit                          | 1000 | 4000 | -    | V/µs |
| dl <sub>com</sub> /dt | rate of change of commutating current | $V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; snubberless condition; gate open circuit; Fig. 12 | -    | 14   | -    | A/ms |

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description                    | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1   | T1     | main terminal 1                | mb                 | T2             |
| 2   | T2     | main terminal 2                | <b>├</b>           | G<br>sym051    |
| 3   | G      | gate                           |                    | Symoor         |
| mb  | Т2     | mounting base; main terminal 2 |                    |                |
|     |        |                                | TO-220AB (SOT78)   |                |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package  |  |         |  |  |  |
|-------------|----------|--|---------|--|--|--|
|             | Name     | Description  | Version |  |  |  |
| BTA208-800B | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |

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## 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                                | Conditions   | Min | Max | Unit |
|---------------------|--|--|-----|-----|------|
| $V_{DRM}$           | repetitive peak off-state voltage        |  | -   | 800 | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3                     | -   | 8   | Α    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5 | -   | 65  | Α    |
|                     |  | full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms                 | -   | 71  | Α    |
| l <sup>2</sup> t    | I <sup>2</sup> t for fusing              | t <sub>p</sub> = 10 ms; SIN  | -   | 21  | A²s  |
| dl <sub>T</sub> /dt | rate of rise of on-state current         | I <sub>G</sub> = 0.2 A   | -   | 100 | A/µs |
| I <sub>GM</sub>     | peak gate current                        |  | -   | 2   | Α    |
| P <sub>GM</sub>     | peak gate power                          |  | -   | 5   | W    |
| P <sub>G(AV)</sub>  | average gate power                       | over any 20 ms period  | -   | 0.5 | W    |
| T <sub>stg</sub>    | storage temperature                      |  | -40 | 150 | °C   |
| Tj                  | junction temperature                     |  | -   | 125 | °C   |

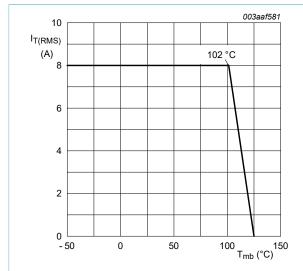


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

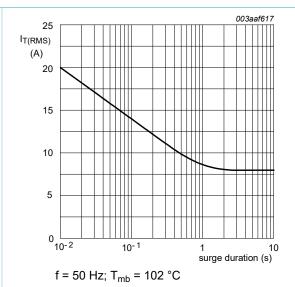


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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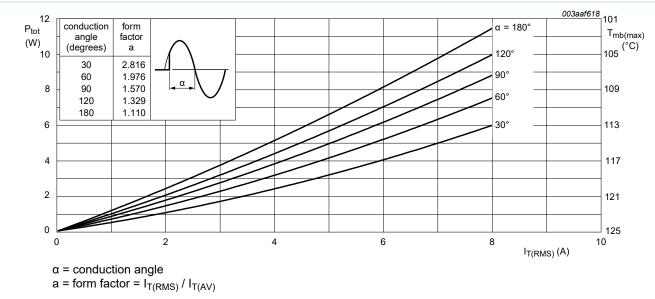


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

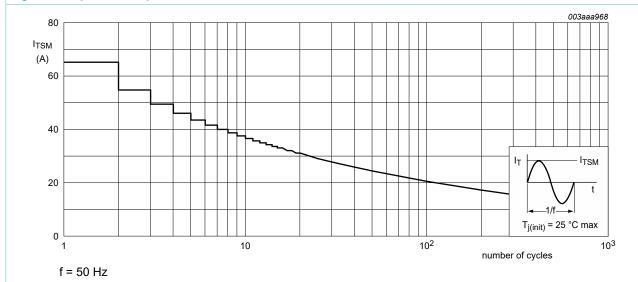
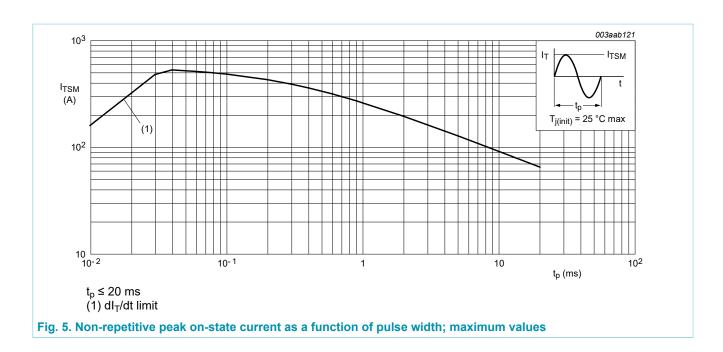


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

| Symbol                | Parameter  | Conditions         | Min | Тур | Max | Unit |
|-----------------------|--|--------------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance   | full cycle; Fig. 6 | -   | -   | 2   | K/W  |
|                       | from junction to mounting base                             | half cycle; Fig. 6 | -   | -   | 2.4 | K/W  |
| $R_{th(j-a)}$         | thermal resistance<br>from junction to<br>ambient free air | in free air        | -   | 60  | -   | K/W  |

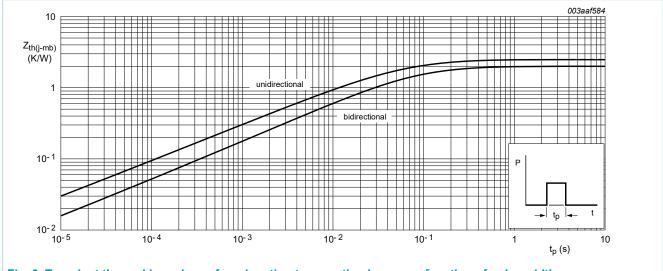


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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## 9. Characteristics

#### **Table 6. Characteristics**

| Symbol                | Parameter                             | Conditions  | Min  | Тур  | Max  | Unit |
|-----------------------|---------------------------------------|---|------|------|------|------|
| Static char           | acteristics                           |   |      |      |      |      |
| I <sub>GT</sub>       | gate trigger current                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 7$   | 2    | 18   | 50   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 \text{ °C}; Fig. 7$                                   | 2    | 21   | 50   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$                   | 2    | 34   | 50   | mA   |
| IL                    | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$                           | -    | 31   | 60   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$                           | -    | 34   | 90   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$                   | -    | 30   | 60   | mA   |
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>  | -    | 31   | 60   | mA   |
| V <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>   | -    | 1.3  | 1.65 | V    |
| $V_{GT}$              | gate trigger voltage                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 11  | -    | 0.7  | 1    | V    |
|                       |                                       | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$<br>Fig. 11  | 0.25 | 0.4  | -    | V    |
| I <sub>D</sub>        | off-state current                     | V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C   | -    | 0.1  | 0.5  | mA   |
| Dynamic cl            | haracteristics                        |   |      |      | 1    | ,    |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 535 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit                    | 1000 | 4000 | -    | V/µs |
| dl <sub>com</sub> /dt | rate of change of commutating current | $V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 20 V/µs; snubberless condition; gate open circuit; Fig. 12 | -    | 14   | -    | A/ms |
| t <sub>gt</sub>       | gate-controlled turn-on time          | $I_{TM}$ = 12 A; $V_D$ = 800 V; $I_G$ = 0.1 A; $dI_G/dt$ = 5 A/ $\mu$ s   | -    | 2    | -    | μs   |

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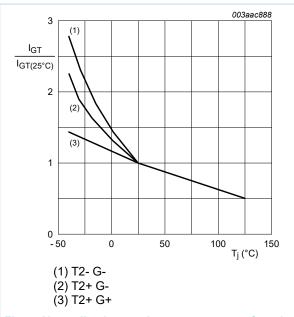


Fig. 7. Normalized gate trigger current as a function of junction temperature

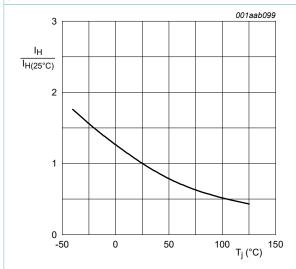


Fig. 9. Normalized holding current as a function of junction temperature

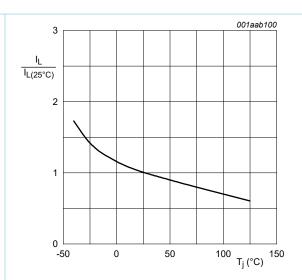
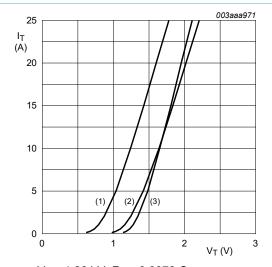


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o$  = 1.264 V;  $R_s$  = 0.0378  $\Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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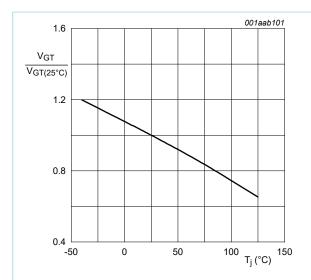


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

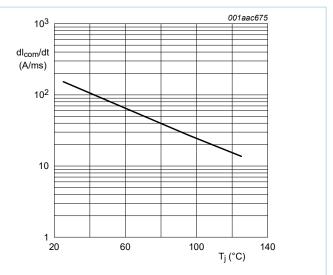
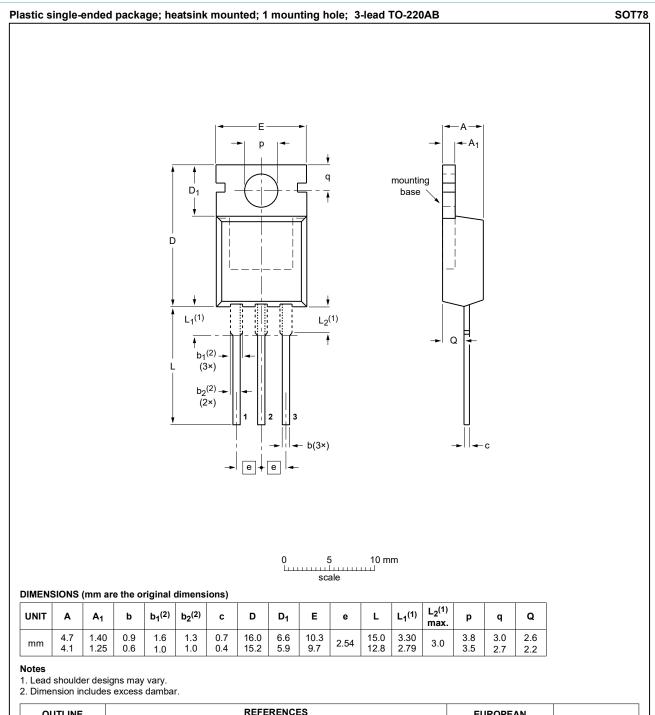


Fig. 12. Rate of rise of commutating current as a function of junction temperature; typical values

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## 10. Package outline



| OUTLINE | REFERENCES |                 |       | EUROPEAN | ISSUE DATE |                                 |
|---------|------------|-----------------|-------|----------|------------|---------------------------------|
| VERSION | IEC        | JEDEC           | JEITA |          | PROJECTION | ISSUE DATE                      |
| SOT78   |            | 3-lead TO-220AB | SC-46 |          |            | <del>08-04-23</del><br>08-06-13 |
|         |            |                 |       |          | - 1        |                                 |

Fig. 13. Package outline TO-220AB (SOT78)

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## 11. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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**3Q Hi-Com Triac** 

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